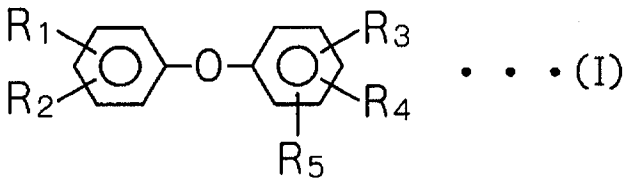
AMENDMENTS TO THE CLAIMS

1. **(Currently Amended)** A developer composition for resists, comprising an organic quaternary ammonium base as a main component,

said developer composition further comprising an anionic surfactant represented by the following general formula (I):



• • • (I)

wherein at least one of R_1 and R_2 represents an alkyl or alkoxy group having 5 to 18 carbon atoms and the other one represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one of R_3, R_4 and R_5 represents an ammonium sulfonate group or a sulfonic acid-substituted ammonium group and the others represent a hydrogen atom, an ammonium sulfonate group or a sulfonic acid-substituted ammonium group;

SO_4^{2-} in an amount from 10 to 10,000 ppm; ~~and~~

a lower alcohol in an amount from 0.05 to 2.5% by mass; and

a halogen ion in an amount of 1,000 ppm or less.

2. **(Canceled)**

3. **(Canceled)**

4. **(Previously presented)** A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 1 to form a resist pattern.

5. (**New**) The developer composition for resists according to claim 1, wherein said lower alcohol has 1 to 5 carbon atoms.

6. (**New**) The developer composition for resists according to claim 5, wherein the lower alcohol is ethanol or methanol.